

FEATURES

- High Power $P_{1dB}=34dBm(TYP.)$
- High Gain $G_{1dB}=28dB(TYP.)$
- High Power Added Efficiency $\eta_{add}=21\%(TYP.)$
- Broadband Operation $f=5.8-7.2GHz.$

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ C$)

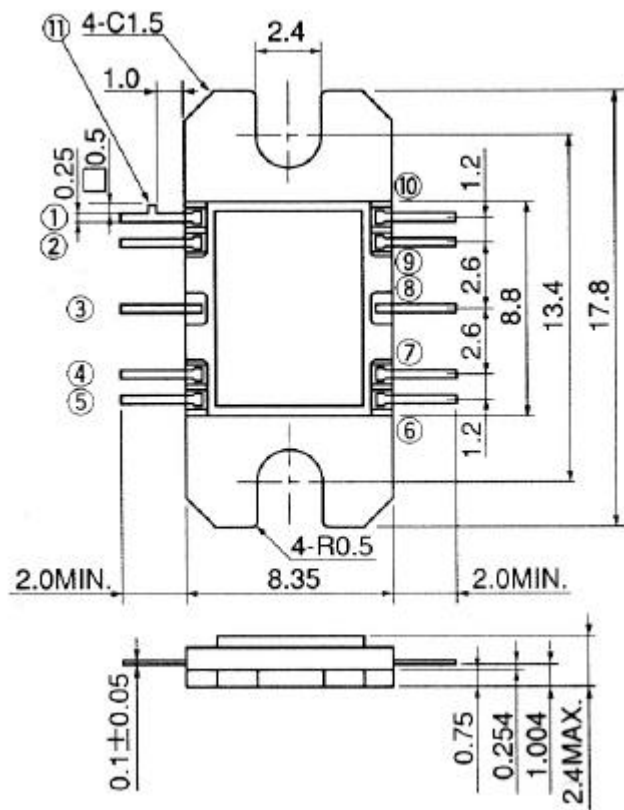
CHARACTERISTICS	SYMBOL	UNIT	RATINGS
DRAIN SUPPLY VOLTAGE	VDD	V	15
GATE SUPPLY VOLTAGE	VGG	V	-10
INPUT POWER	Pin	dBm	10
FLANGE TEMPERATURE	Tf	°C	-30 - +80
STORAGE TEMPERATURE	Tstg	°C	-65 - +175

RF PERFORMANCE SPECIFICATIONS ($T_a=25^\circ C$)

CHARACTERISTICS	SYMBOL	CONDITION	UNIT	MIN.	TYP.	MAX.
Operating Frequency	f	VDD=10V VGG=-5V	GHz	5.8	—	7.2
Output Power at 1dB Gain Compression Point	P1dB		dBm	32	34	—
Power Gain at 1dB Gain Compression Point	G1dB		dB	25	28	—
Gain Flatness	G		dB	—	—	±2.0
Drain Current	IDD		A	—	1.2	1.6
Power Added Efficiency	η_{add}		%	—	21	—
VSWRin (small signal)	VSWRin		—	—	2.0:1	3.0:1

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Package Outline



Unit in mm

①④⑤⑥⑨⑩: No Connection

③: RF Input

②: VGG

⑦: VDD

⑧: RF Output

11pin: Orientation Tab

Recommended Bias Configuration

